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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

2014	
Product Status	Active
Core Processor	MAXQ20S
Core Size	16-Bit
Speed	12MHz
Connectivity	SPI, UART/USART
Peripherals	Brown-out Detect/Reset, Infrared, Power-Fail, POR, WDT
Number of I/O	32
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	0°C ~ 70°C (TA)
Mounting Type	Surface Mount
Package / Case	44-WFQFN Exposed Pad
Supplier Device Package	44-TQFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/analog-devices/maxq610j-0000

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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## **RECOMMENDED DC OPERATING CONDITIONS (continued)**

 $(V_{DD} = V_{RST} \text{ to } 3.6V, T_A = 0^{\circ}C \text{ to } +70^{\circ}C.)$  (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS	
Input High Voltage for HFXIN	VIH_HFXIN		0.7 x V <sub>DD</sub>		V <sub>DD</sub>	V	
IRRX Input Filter Pulse-Width Reject					50	ns	
IRRX Input Filter Pulse-Width Accept	t <sub>IRRX_A</sub>		300			ns	
		V <sub>DD</sub> = 3.6V, I <sub>OL</sub> = 25mA (Note 5)			1.0		
Output Low Voltage for IRTX	Vol_irtx	V <sub>DD</sub> = 2.35V, I <sub>OL</sub> = 10mA (Note 5)			1.0	V	
		$V_{DD} = 1.85V, I_{OL} = 4.5mA$			1.0		
		V <sub>DD</sub> = 3.6V, I <sub>OL</sub> = 11mA (Note 5)		0.4	0.5		
Output Low Voltage for RESET and All Port Pins (Note 10)	VOL	V <sub>DD</sub> = 2.35V, I <sub>OL</sub> = 8mA (Note 5)		0.4	0.5	V	
and An Orthins (Note 10)		V <sub>DD</sub> = 1.85V, I <sub>OL</sub> = 4.5mA		0.4	0.5		
Output High Voltage for IRTX and All Port Pins	Vон	I <sub>OH</sub> = -2mA	V <sub>DD</sub> - 0.5		V <sub>DD</sub>	V	
Input/Output Pin Capacitance for All Port Pins	CIO	(Note 5)			15	pF	
Input Leakage Current	١L	Internal pullup disabled	-100		+100	nA	
Input Pullup Resistor for RESET,		V <sub>DD</sub> = 3.0V, V <sub>OL</sub> = 0.4V (Note 5)	16 28 39				
IRTX, IRRX, and All Port Pins	R <sub>PU</sub>	$V_{DD} = 2.0V, V_{OL} = 0.4V$	17	30	41	- kΩ	
EXTERNAL CRYSTAL/RESONAT	OR		1			1	
Crystal/Resonator	<b>f</b> HFXIN		1		12	MHz	
Crystal/Resonator Period	<b>t</b> HFXIN			1/f <sub>HFXIN</sub>		ns	
Crystal/Resonator Warmup Time	txtal_rdy	From initial oscillation	8	192 x t <sub>HFX</sub>	IN	ms	
Oscillator Feedback Resistor	Roscf	(Note 5)	0.5 1.0 1.			MΩ	
EXTERNAL CLOCK INPUT			•				
External Clock Frequency	fxclk		DC		12	MHz	
External Clock Period	txclk			1/fxclk		ns	
External Clock Duty Cycle	txclk_duty		45		55	%	
System Clock Frequency	fск			<b>f</b> HFIN		MHz	
bystem block riequency		HFXOUT = GND		fxclk			
System Clock Period	tск			1/fCK		MHz	
NANOPOWER RING OSCILLATO	R						
Nanopower Ring Oscillator	f <sub>NANO</sub>	$T_{A} = +25^{\circ}C$	3.0	8.0	20.0	kHz	
Frequency	UNANU	$T_A = +25^{\circ}C$ , $V_{DD} = POR$ voltage (Note 5)	1.7	2.4			
Nanopower Ring Oscillator Duty Cycle	t <sub>NANO</sub>	(Note 5)	40		60	%	
Nanopower Ring Oscillator		Typical at V <sub>DD</sub> = 1.64V, T <sub>A</sub> = +25°C (Note 5)		40	400	nA	

## SPI ELECTRICAL CHARACTERISTICS

 $(V_{DD} = V_{RST}$  to 3.6V,  $T_A = 0^{\circ}C$  to +70°C. AC electrical specifications are guaranteed by design and are not production tested.)

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
SPI Master Operating Frequency	1/t <sub>MCK</sub>				f <sub>CK</sub> /2	MHz
SPI Slave Operating Frequency	1/tsck				f <sub>CK</sub> /4	MHz
SPI I/O Rise/Fall Time	t <sub>SPI_RF</sub>	$C_L = 15 pF$ , pullup = 560 $\Omega$	8.3		23.6	ns
SCLK Output Pulse-Width High/Low	t <sub>MCH</sub> , t <sub>MCL</sub>		t <sub>MCK</sub> /2 - tSPI_RF			ns
MOSI Output Hold Time After SCLK Sample Edge	tмон		t <sub>MCK</sub> /2 - t <sub>SPI_RF</sub>			ns
MOSI Output Valid to Sample Edge	tmov		t <sub>MCK</sub> /2 - t <sub>SPI_RF</sub>			ns
MISO Input Valid to SCLK Sample Edge Rise/Fall Setup	tMIS		25			ns
MISO Input to SCLK Sample Edge Rise/Fall Hold	tMIH		0			ns
SCLK Inactive to MOSI Inactive	tMLH		t <sub>MCK</sub> /2 - t <sub>SPI_RF</sub>			ns
SCLK Input Pulse-Width High/Low	tSCH, tSCL			t <sub>SCK</sub> /2		ns
SSEL Active to First Shift Edge	tsse		tspi_rf			ns
MOSI Input to SCLK Sample Edge Rise/Fall Setup	tsis		tSPI_RF			ns
MOSI Input from SCLK Sample Edge Transition Hold	tsih		tspi_rf			ns
MISO Output Valid After SCLK Shift Edge Transition	tsov			:	2tspi_rf	ns
SSEL Inactive	tssh		t <sub>CK</sub> + t <sub>SPI_RF</sub>			ns
SCLK Inactive to SSEL Rising	t <sub>SD</sub>		tspi_rf			ns
MISO Output Disabled After SSEL Edge Rise	tslh			:	2t <sub>CK</sub> + 2t <sub>SPI_RF</sub>	ns

## **Pin Description**

PIN			FUNCTION		
32 TQFN	2 TQFN 40 TQFN 44 TQFN		NAME	FUNCTION	
				POWER PINS	
15, 29	18, 38	19, 41	V <sub>DD</sub>	Supply Voltage	
13, 22, 30	_	17, 20, 28, 42	GND	<b>Ground.</b> These pins must be directly connected to the ground plane. The 40-pin TQFN package does not have any ground pins and connects to ground through the exposed pad.	
14	17	18	REGOUT	<b>Regulator Capacitor.</b> This pin must be connected to ground through a $1.0\mu$ F external ceramic-chip capacitor. The capacitor must be placed as close to this pin as possible. No devices other than the capacitor should be connected to this pin.	
			EP	<b>Exposed Pad.</b> For the 32-pin TQFN package, leave unconnected. For the 40-pin TQFN package, the exposed pad is internally connected to GND. Connect to the ground plane. For the 44-pin TQFN package, the EP has no internal connection to the device. Leave unconnected. Not intended as an electrical connection point.	
			I	RESET PINS	
28	37	40	RESET	<b>Digital, Active-Low, Reset Input/Output.</b> The CPU is held in reset when this pin is low and begins executing from the reset vector when released. The pin includes pullup current source and should be driven by an open-drain, external source capable of sinking in excess of 4mA. This pin is driven low as an output when an internal reset condition occurs.	
	I		1	CLOCK PINS	
18	21	23	HFXIN	<b>High-Frequency Crystal Input.</b> Connect external crystal or resonator between HFXIN and HFXOUT as the high-frequency system clock. Alternatively, HFXIN is	
19	22	24	HFXOUT	the input for an external, high-frequency clock source when HFXOUT is unconnected.	
			•	IR FUNCTION PINS	
31	39	43	IRTX	<b>IR Transmit Output.</b> IR transmit pin capable of sinking 25mA. This pin defaults to high-impedance input with the weak pullup disabled during all forms of reset. Software must configure this pin after release from reset to remove the high-impedance input condition.	
32	40	44	IRRX	<b>IR Receive Input.</b> IR receive pin. This pin defaults to high-impedance input with the weak pullup disabled during all forms of reset. Software must configure this pin after release from reset to remove the high-impedance input condition.	

## Pin Description (continued)

Р	IN					-			
32 TQFN	40 TQFN	44 TQFN	NAME			Г	UNCTION		
24–27	25, 26, 29–32,	27, 29, 32–35,	P2.0– P2.7; MOSI, MISO, SCLK,	<ul> <li>General-Purpose, Digital, I/O, Type-C Port. These port pins function as bidirectional I/O pins. P2.0–P2.3 default to high-impedance mode after a reset. Software must configure these pins after release from reset to remove the high-impedance input condition. All alternate functions must be enabled from software. Enabling the pin's special function disables the general-purpose I/O on the pin.</li> <li>The JTAG pins (P2.4–P2.7) default to their JTAG function with weak pullups enabled after a reset. The JTAG function can be disabled using the TAP bit in the SC register.</li> <li>P2.7 functions as the JTAG test-data output on reset and defaults to an input with a weak pullup. The output function of the test data is only enabled during the TAP's Shift_IR or Shift_DR states.</li> </ul>					
	35, 36	38, 39	SSEL,	32 TQFN	40 TQFN	44 TQFN	PORT	SPECIAL FUNCTION	
			TCK, TDI, TMS,	_	25	27	P2.0	MOSI	
			TDO	_	26	29	P2.1	MISO	
				_	29	32	P2.2	SCLK	
				_	30	33	P2.3	SSEL	
				24	31	34	P2.4	ТСК	
				25	32	35	P2.5	TDI	
				26	35	38	P2.6	TMS	
				27	36	39	P2.7	TDO	
				These port default to h pins after re	pins functior igh-impedan elease from r	n as bidirecti ce mode afte eset to remo	onal I/O pins o er a reset. Softv	al Edge-Selectable Interrupt. r as interrupts. All port pins vare must configure these pedance input condition. All SPECIAL FUNCTION	
	0 4 15	2, 4, 15,	P3.0-	JZ TQIT	2	2	P3.0	INT8	
_	2, 4, 15, 16, 27,	16, 30,	P3.7;		4	4	P3.1	INT9	
	28, 33, 34	31, 36,	INT8-		15	15	P3.2	INT10	
		37	INT15		16	16	P3.3	INT18	
					27	30	P3.4	INT12	
					28	31	P3.5	INT12	
				<u> </u>	33	36	P3.6	INT14	
					34	37	P3.7	INT14	
		1	1				10.7	111110	
23			N.C.	1		-	una Lagua thir	s pin unconnected.	

MAXQ610

AREA	PAGE ADDRESS	MAXIMUM PRIVILEGE LEVEL
System	0 to ULDR-1	High
User Loader	ULDR to UAPP-1	Medium
User Application	UAPP to top	Low
Utility ROM	N/A	High
Other (RAM)	N/A	Low

Table 1. Memory Areas and Associated Maximum Privilege Levels

#### **Memory Protection**

The optional memory-protection feature separates code memory into three areas: system, user loader, and user application. Code in the system area can be kept confidential. Code in the user areas can be prevented from reading and writing system code. The user loader can also be protected from user application code.

Memory protection is implemented using privilege levels for code. Each area has an associated privilege level. RAM/ROM are assigned privilege levels as well. Refer to the *MAXQ610 User's Guide* for a more thorough explanation of the topic. See Table 1.

#### **Stack Memory**

A 16-bit-wide internal stack provides storage for program return addresses and can also be used general-purpose data storage. The stack is used automatically by the processor when the CALL, RET, and RETI instructions are executed and when an interrupt is serviced. An application can also store values in the stack explicitly by using the PUSH, POP, and POPI instructions.

On reset, the stack pointer, SP, initializes to the top of the stack (0Fh). The CALL, PUSH, and interrupt-vectoring operations increment SP, then store a value at the location pointed to by SP. The RET, RETI, POP, and POPI operations retrieve the value at SP and then decrement SP.

#### Utility ROM

The utility ROM is a 5.25KB block of internal ROM memory that defaults to a starting address of 8000h. The utility ROM consists of subroutines that can be called from application software. These include the following:

- In-system programming (bootstrap loader) using JTAG interface
- In-circuit debug routines
- Test routines (internal memory tests, memory loader, etc.)
- User-callable routines for in-application flash programming and fast table lookup

Following any reset, execution begins in the utility ROM.

The ROM software determines whether the program execution should immediately jump to location 0000h, the start of system code, or to one of the special routines mentioned. Routines within the utility ROM are user accessible and can be called as subroutines by the application software. More information on the utility ROM functions is contained in the *MAXQ610 User's Guide*.

Some applications require protection against unauthorized viewing of program code memory. For these applications, access to in-system programming, inapplication programming, or in-circuit debugging functions is prohibited until a password has been supplied. The password is defined as the 16 words of physical program memory at addresses 0010h to 001Fh.

Three password locks are provided for protection of up to three different program memory segments. When the PWL is set to 1 (POR default) and the contents of the memory at addresses 0010h to 001Fh are any value other than FFh or 00h, the password is required to access the utility ROM, including in-circuit debug and in-system programming routines that allow reading or writing of internal memory. When PWL is cleared to 0, these utilities are fully accessible without password. The password is automatically set to all ones following a mass erase.

## Watchdog Timer

An internal watchdog timer greatly increases system reliability. The timer resets the device if software execution is disturbed. The watchdog timer is a free-running counter designed to be periodically reset by the application software. If software is operating correctly, the counter is periodically reset and never reaches its maximum count. However, if software operation is interrupted, the timer does not reset, triggering a system reset and optionally a watchdog timer interrupt. This protects the system against electrical noise or ESD upsets that could cause uncontrolled processor operation. The internal watchdog timer is an upgrade to older designs with external watchdog devices, reducing system cost and simultaneously increasing reliability.



WD[1:0]	WATCHDOG CLOCK	WATCHDOG INTERRUPT TIMEOUT	WATCHDOG RESET AFTER WATCHDOG INTERRUPT (µs)
00	SyscIk/2 <sup>15</sup>	2.7ms	42.7
01	SyscIk/2 <sup>18</sup>	21.9ms	42.7
10	SyscIk/2 <sup>21</sup>	174.7ms	42.7
11	SyscIk/2 <sup>24</sup>	1.4s	42.7

#### Table 2. Watchdog Interrupt Timeout (Sysclk = 12MHz, CD[1:0] = 00)

The watchdog timer functions as the source of both the watchdog-timer timeout and the watchdog-timer reset. The timeout period can be programmed in a range of  $2^{15}$  to  $2^{24}$  system clock cycles. An interrupt is generated when the timeout period expires if the interrupt is enabled. All watchdog-timer resets follow the programmed interrupt timeouts by 512 system clock cycles. If the watchdog timer is not restarted for another full interval in this time period, a system reset occurs when the reset timeout expires. See Table 2.

## IR Carrier Generation and Modulation Timer

The dedicated IR timer/counter module simplifies lowspeed IR communication. The IR timer implements two pins (IRTX and IRRX) for supporting IR transmit and receive, respectively. The IRTX pin has no corresponding port pin designation, so the standard PD, PO, and PI port control status bits are not present. However, the IRTX pin output can be manipulated high or low using the PWCN.IRTXOUT and PWCN.IRTXOE bits when the IR timer is not enabled (i.e., IREN = 0).

The IR timer is composed of two separate timing entities: a carrier generator and a carrier modulator. The carrier generation module uses the 16-bit IR Carrier register (IRCA) to define the high and low time of the carrier through the IR carrier high byte (IRCAH) and IR carrier low byte (IRCAL). The carrier modulator uses the IR data bit (IRDATA) and IR Modulator Time register (IRMT) to determine whether the carrier or the idle condition is present on IRTX.

The IR timer is enabled when the IR enable bit (IREN) is set to 1. The IR Value register (IRV) defines the beginning value for the carrier modulator. During transmission, the IRV register is initially loaded with the IRMT value and begins down counting towards 0000h, whereas in receive mode it counts upward from the initial IRV register value. During the receive operation, the IRV register can be configured to reload with 0000h when capture occurs on detection of selected edges or can be allowed to continue free-running throughout the receive operation. An overflow occurs when the IR timer value rolls over from 0FFFFh to 0000h. The IR overflow flag (IROV) is set to 1 and an interrupt is generated if enabled (IRIE = 1).

#### **Carrier Generation Module**

The IRCAH byte defines the carrier high time in terms of the number of IR input clocks, whereas the IRCAL byte defines the carrier low time.

> IR Input Clock (f<sub>IRCLK</sub>) = f<sub>SYS</sub>/2<sup>IRDIV[1:0]</sup> Carrier Frequency (f<sub>CARRIER</sub>) = f<sub>IRCLK</sub>/(IRCAH + IRCAL + 2) Carrier High Time = IRCAH + 1

> > Carrier Low Time = IRCAL + 1

Carrier Duty Cycle = (IRCAH + 1)/(IRCAH + IRCAL + 2)

During transmission, the IRCA register is latched for each IRV downcount interval and is sampled along with the IRTXPOL and IRDATA bits at the beginning of each new IRV downcount interval so that duty-cycle variation and frequency shifting is possible from one interval to the next, which is illustrated in Figure 1.

Figure 2 illustrates the basic carrier generation and its path to the IRTX output pin. The IR transmit polarity bit (IRTXPOL) defines the starting/idle state and the carrier polarity of the IRTX pin when the IR timer is enabled.

#### **IR Transmission**

During IR transmission (IRMODE = 1), the carrier generator creates the appropriate carrier waveform, while the carrier modulator performs the modulation. The carrier modulation can be performed as a function of carrier cycles or IRCLK cycles dependent on the setting of the IRCFME bit. When IRCFME = 0, the IRV downcounter is clocked by the carrier frequency and thus the modulation is a function of carrier cycles. When IRCFME = 1, the IRV downcounter is clocked by IRCLK, allowing carrier modulation timing with IRCLK resolution.

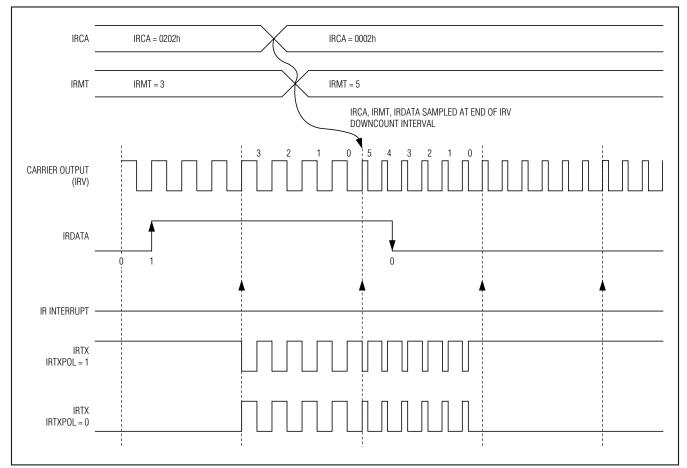


Figure 1. IR Transmit Frequency Shifting Example (IRCFME = 0)

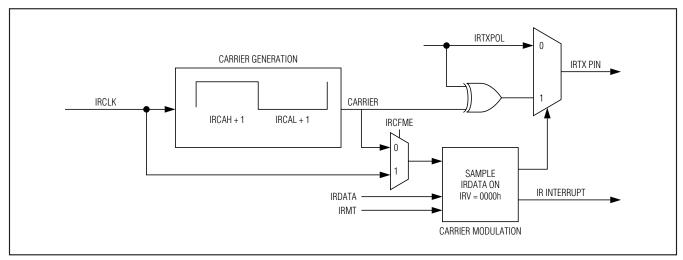


Figure 2. IR Transmit Carrier Generation and Carrier Modulator Control

///XI/M

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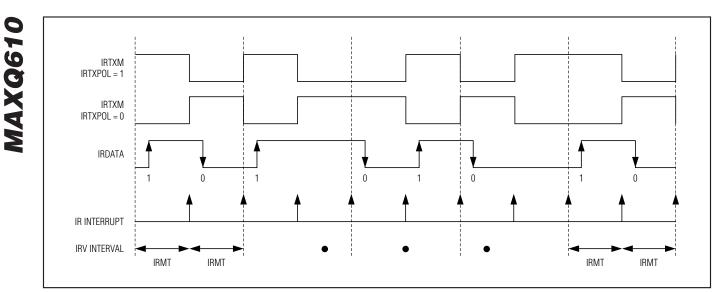


Figure 4. External IRTXM (Modulator) Output

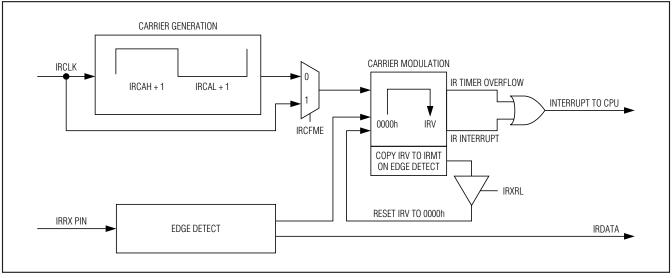


Figure 5. IR Capture

#### **IR Receive**

When configured in receive mode (IRMODE = 0), the IR hardware supports the IRRX capture function. The IRRXSEL[1:0] bits define which edge(s) of the IRRX pin should trigger IR timer capture function.

The IR module starts operating in the receive mode when IRMODE = 0 and IREN = 1. Once started, the IR timer (IRV) starts up counting from 0000h when a quali-

fied capture event as defined by IRRXSEL happens. The IRV register is, by default, counting carrier cycles as defined by the IRCA register. However, the IR carrier frequency detect (IRCFME) bit can be set to 1 to allow clocking of the IRV register directly with the IRCLK for finer resolution. When IRCFME = 0, the IRCA defined carrier is counted by IRV. When IRCFME = 1, the IRCLK clocks the IRV register.

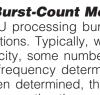
On the next gualified event, the IR module does the following:

- 1) Captures the IRRX pin state and transfers its value to IRDATA. If a falling edge occurs, IRDATA = 0. If a rising edge occurs, IRDATA = 1.
- 2) Transfers its current IRV value to the IRMT.
- 3) Resets IRV content to 0000h (if IRXRL = 1).
- 4) Continues counting again until the next qualified event.

If the IR timer value rolls over from 0FFFFh to 0000h before a qualified event happens, the IR timer overflow (IROV) flag is set to 1 and an interrupt generated if enabled. The IR module continues to operate in receive mode until it is stopped by switching into transmit mode (IRMODE = 1) or clearing IREN = 0.

#### **Carrier Burst-Count Mode**

A special mode reduces the CPU processing burden when performing IR learning functions. Typically, when operating in an IR learning capacity, some number of carrier cycles are examined for frequency determination. Once the frequency has been determined, the IR receive function can be reduced to counting the number of carrier pulses in the burst and the duration of the combined mark-space time within the burst. To simplify this process, the receive burst-count mode (as enabled by the RXBCNT bit) can be used. When RXBCNT = 0, the standard IR receive capture functionality is in place.



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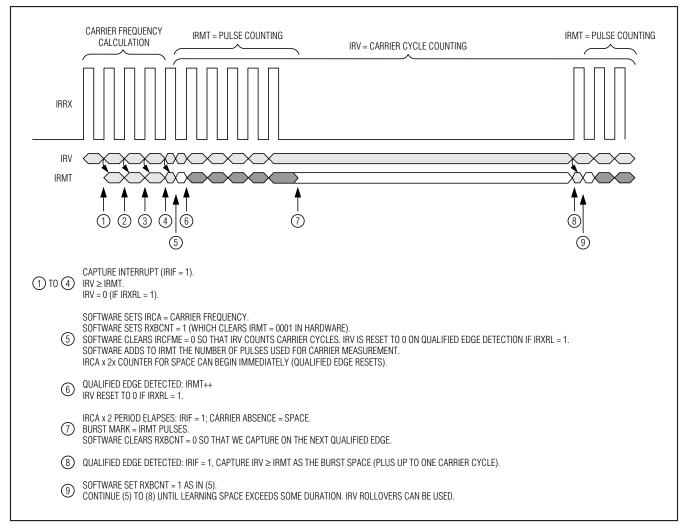


Figure 6. Receive Burst-Count Example



## **On-Chip Oscillator**

An external quartz crystal or a ceramic resonator can be connected between HFXIN and HFXOUT on the MAXQ610, as illustrated in Figure 9.

Noise at HFXIN and HFXOUT can adversely affect onchip clock timing. It is good design practice to place the crystal and capacitors near the oscillator circuitry and connect HFXIN and HFXOUT to ground with a direct short trace. The typical values of external capacitors vary with the type of crystal to be used and should be initially selected based on the load capacitance as suggested by the crystal manufacturer.

#### **ROM Loader**

The MAXQ610 includes a ROM loader. The loader denies access to the system, user loader, or user-application memories unless an area-specific password is provided. The ROM loader is not available in ROM-only versions of the MAXQ610.

#### Loading Flash Memory

An internal bootstrap loader allows the device to be reloaded over a simple JTAG interface. As a result, software can be upgraded in-system, eliminating the need for a costly hardware retrofit when updates are required. Remote software uploads are possible that enable physically inaccessible applications to be frequently updated. The interface hardware can be a JTAG connection to another microcontroller, or a connection to a PC serial port using a serial-to-JTAG converter, such as the MAXQJTAG-001 available from Maxim Integrated Products. If in-system programmability is not required, a commercial gang programmer can be used for mass programming. Activating the JTAG interface and loading the test access port (TAP) with the system programming instruction invokes the bootstrap loader. Setting the SPE bit to 1 during reset through the JTAG interface executes the bootstraploader-mode program that resides in the utility ROM. When programming is complete, the bootstrap loader can clear the SPE bit and reset the device, allowing the device to bypass the utility ROM and begin execution of the application software.

In addition, the ROM loader also enforces the memoryprotection policies. 16-word passwords are required to access the ROM loader interface.

Loading memory is not possible for ROM-only versions of the MAXQ610 family.

## In-Application Flash Programming

From user-application code, flash can be programmed using the ROM utility functions from either C or assembly language. The function declarations that follow show examples of some of the ROM utility functions provided for in-application flash programming.

/\* Write one 16-bit word to code address 'dest'.

- \* Dest must be aligned to 16 bits.
- \* Returns 0 = failure, 1 = OK.
- \* /

int flash write (uint16 t dest, uint16 t data);

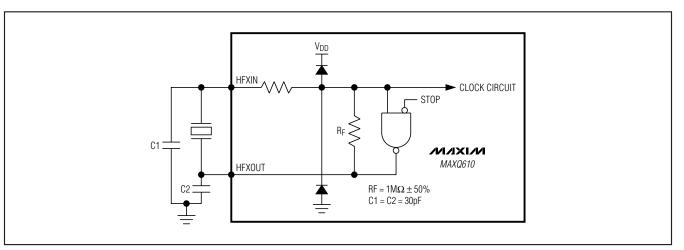


Figure 9. On-Chip Oscillator

To erase, the following function would be used:

 $/\star\,$  Erase the given Flash page

```
* addr: Flash offset (anywhere within page)
*/
```

```
int flash_erasepage(uint16_t addr);
```

The in-application flash programming must call ROM utility functions to erase and program any of the flash memory. Memory protection is enforced by the ROM utility functions.

In-application programming is not available in ROMonly versions of the MAXQ610 family.

## In-Circuit Debug and JTAG Interface

Embedded debug hardware and software are developed and integrated into the MAXQ610 to provide full in-circuit debugging capability in a user application environment. These hardware and software features include:

- A debug engine.
- A set of registers providing the ability to set breakpoints on register, code, or data using debug service routines stored in ROM.

Collectively, these hardware and software features support two modes of in-circuit debug functionality:

- 1) Background Mode
  - CPU is executing the normal user program.
  - Allows the host to configure and set up the in-circuit debugger.
- 2) Debug Mode
  - The debugger takes over the control of the CPU.
  - Read/write accesses to internal registers and memory.
  - Single-step of the CPU for trace operation.

The interface to the debug engine is the TAP controller. The interface allows for communication with a bus master that can either be automatic test equipment or a component that interfaces to a higher level test bus as part of a complete system. The communication operates across a 4-wire serial interface from a dedicated TAP that is compatible to the JTAG IEEE Std 1149. The TAP provides an independent serial channel to communicate synchronously with the host system.

To prevent unauthorized access of the protected memory regions through the JTAG interface, the debug engine prevents modification of the privilege registers and disallows all access to system memory, unless memory protection is disabled. In addition, all services (such as register display or modification) are denied when code is executing inside the system area.

The debugger is not available for ROM-only versions of the MAXQ610 family.

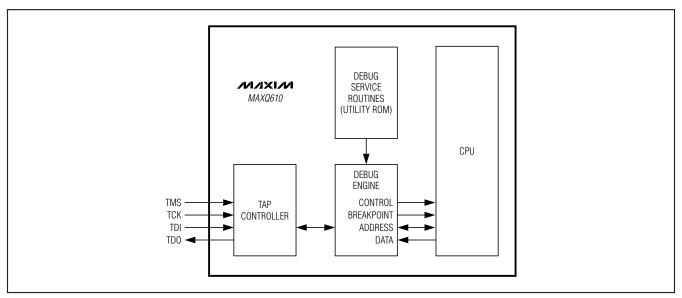


Figure 10. In-Circuit Debugger

## **Operating Modes**

The lowest power mode of operation for the MAXQ610 is stop mode. In this mode, CPU state and memories are preserved, but the CPU is not actively running. Wake-up sources include external I/O interrupts, the power-fail warning interrupt, or a power-fail reset. Any time the microcontroller is in a state where code does not need to be executed, the user software can put the MAXQ610 into stop mode. The nanopower ring oscillator is an internal ultra-low-power (400nA), 8kHz ring oscillator that can be used to drive a wake-up timer that exits stop mode. The wake-up timer is programmable by software in steps of 125µs up to approximately 8s.

The power-fail monitor is always on during normal operation. However, it can be selectively disabled during stop mode to minimize power consumption. This feature is enabled using the power-fail monitor disable (PFD) bit in the PWCN register. The reset default state for the PFD bit is 1, which disables the power-fail monitor function during stop mode. If power-fail monitoring is disabled (PFD = 1) during stop mode, the circuitry responsible for generating a power-fail warning or reset is shut down and neither condition is detected. Thus, the V<sub>DD</sub> < V<sub>RST</sub> condition does not invoke a reset state. However, in the event that V<sub>DD</sub> falls below the POR level, a POR is generated. The power-fail monitor is enabled prior to stop mode exit and before code execution begins. If a power-fail warning condition (V<sub>DD</sub> < V<sub>PFW</sub>) is then detected, the power-fail interrupt flag is set on stop mode exit. If a power-fail condition is detected (V<sub>DD</sub> < V<sub>RST</sub>), the CPU goes into reset.

#### **Power-Fail Detection**

Figures 11, 12, and 13 show the power-fail detection and response during normal and stop mode operation.

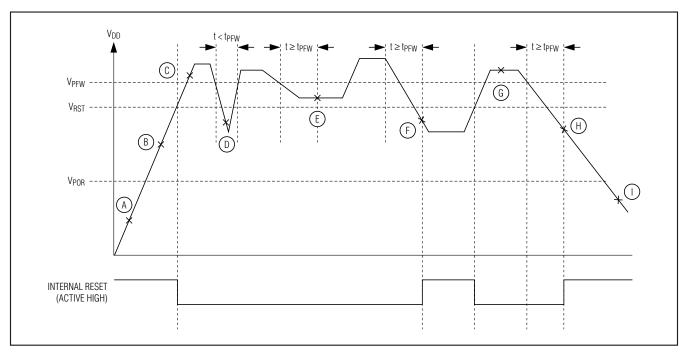


Figure 11. Power-Fail Detection During Normal Operation

STATE	POWER-FAIL	INTERNAL REGULATOR	CRYSTAL OSCILLATOR	SRAM RETENTION	COMMENTS
A	On	Off	Off	—	V <sub>DD</sub> < V <sub>POR</sub> .
В	On	On	On		V <sub>POR</sub> < V <sub>DD</sub> < V <sub>RST.</sub> Crystal warmup time, t <sub>XTAL_RDY</sub> . CPU held in reset.
С	On	On	On	_	V <sub>DD</sub> > V <sub>RST</sub> . CPU normal operation.
D	On	On	On	_	Power drop too short. Power-fail not detected.
E	On	On	On	_	$\label{eq:VRST} \begin{array}{l} V_{\text{RST}} < V_{\text{DD}} < V_{\text{PFW}}. \\ PFI \text{ is set when } V_{\text{RST}} < V_{\text{DD}} < V_{\text{PFW}} \text{ and maintains} \\ this state for at least  t_{\text{PFW}}, at which time a power-fail interrupt is generated (if enabled). \\ CPU \ continues \ normal operation. \end{array}$
F	On (Periodically)	Off	Off	Yes	VPOR < VDD < VRST. Power-fail detected. CPU goes into reset. Power-fail monitor turns on periodically.
G	On	On	On		V <sub>DD</sub> > V <sub>RST.</sub> Crystal warmup time, t <sub>XTAL_RDY</sub> . CPU resumes normal operation from 8000h.
н	On (Periodically)	Off	Off	Yes	V <sub>POR</sub> < V <sub>DD</sub> < V <sub>RST.</sub> Power-fail detected. CPU goes into reset. Power-fail monitor is turned on periodically.
I	Off	Off	Off		V <sub>DD</sub> < V <sub>POR.</sub> Device held in reset. No operation allowed.

## Table 4. Power-Fail Detection States During Normal Operation

If a reset is caused by a power-fail, the power-fail monitor can be set to one of the following intervals:

- Always on—continuous monitoring
- 2<sup>11</sup> nanopower ring oscillator clocks (~256ms)
- 2<sup>12</sup> nanopower ring oscillator clocks (~512ms)
- 2<sup>13</sup> nanopower ring oscillator clocks (~1.024s)

In the case where the power-fail circuitry is periodically turned on, the power-fail detection is turned on for two nanopower ring oscillator cycles. If  $V_{DD} > V_{RST}$  during

detection, V<sub>DD</sub> is monitored for an additional nanopower ring oscillator period. If V<sub>DD</sub> remains above V<sub>RST</sub> for the third nanopower ring period, the CPU exits the reset state and resumes normal operation from utility ROM at 8000h after satisfying the crystal warmup period.

If a reset is generated by any other event, such as the RESET pin being driven low externally or the watchdog timer, the power-fail, internal regulator, and crystal remain on during the CPU reset. In these cases, the CPU exits the reset state in less than 20 crystal cycles after the reset source is removed.

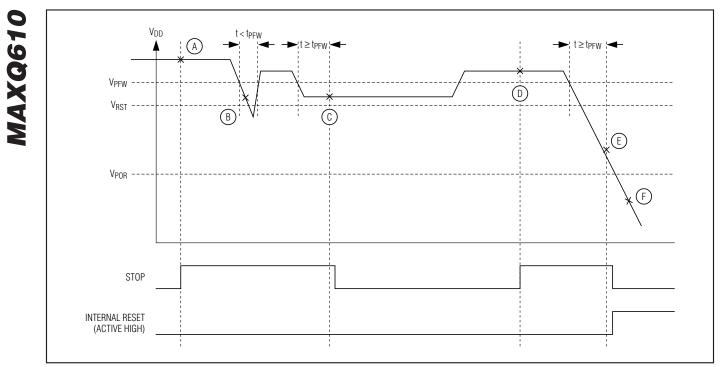


Figure 12. Stop Mode Power-Fail Detection States with Power-Fail Monitor Enabled

Table 5. Stop Mode Power-Fail Detection	n States with Power-Fail Monitor Enabled
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STATE	POWER-FAIL	INTERNAL REGULATOR	CRYSTAL OSCILLATOR	SRAM RETENTION	COMMENTS
A	On	Off	Off	Yes	Application enters stop mode. VDD > VRST. CPU in stop mode.
В	On	Off	Off	Yes	Power drop too short. Power-fail not detected.
С	On	On	On	Yes	V <sub>RST</sub> < V <sub>DD</sub> < V <sub>PFW</sub> . Power-fail warning detected. Turn on regulator and crystal. Crystal warmup time, t <sub>XTAL_RDY</sub> . Exit stop mode.
D	On	Off	Off	Yes	Application enters stop mode. VDD > VRST. CPU in stop mode.
E	On (Periodically)	Off	Off	Yes	V <sub>POR</sub> < V <sub>DD</sub> < V <sub>RST.</sub> Power-fail detected. CPU goes into reset. Power-fail monitor is turned on periodically.
F	Off	Off	Off	_	V <sub>DD</sub> < V <sub>POR</sub> . Device held in reset. No operation allowed.



Table 6. Stop Mode Power-Fail Detection States with Power-Fail Monitor Disabled (continued)

STATE	POWER-FAIL	INTERNAL REGULATOR	CRYSTAL OSCILLATOR	SRAM RETENTION	COMMENTS
D	Off	Off	Off	Yes	Application enters stop mode. V <sub>DD</sub> > V <sub>RST</sub> . CPU in stop mode.
E	On (Periodically)	Off	Off	Yes	VPOR < VDD < VRST. An interrupt occurs that causes the CPU to exit stop mode. Power-fail monitor is turned on, detects a power- fail, puts CPU in reset. Power-fail monitor is turned on periodically.
F	Off	Off	Off		V <sub>DD</sub> < V <sub>POR</sub> Device held in reset. No operation allowed.

## \_Applications Information

The low-power, high-performance RISC architecture of this device makes it an excellent fit for many portable or battery-powered applications. It is ideally suited for applications such as universal remote controls that require the cost-effective integration of IR transmit/ receive capability.

#### **Grounds and Bypassing**

Careful PCB layout significantly minimizes system-level digital noise that could interact with the microcontroller or peripheral components. The area under any digital components should be a continuous ground plane if possible. Keep any bypass capacitor leads short for best noise rejection and place the capacitors as close to the leads of the devices as possible.

CMOS design guidelines for any semiconductor require that no pin be taken above  $V_{DD}$  or below GND. Violation of this guideline can result in a hard failure (damage to the silicon inside the device) or a soft failure (unintentional modification of memory contents). Voltage spikes above or below the device's absolute maximum ratings can potentially cause a devastating IC latchup.

Microcontrollers commonly experience negative voltage spikes through either their power pins or generalpurpose I/O pins. Negative voltage spikes on power pins are especially problematic as they directly couple to the internal power buses. Devices such as keypads can conduct electrostatic discharges directly into the microcontroller and seriously damage the device. System designers must protect components against these transients that can corrupt system memory.

## \_Differences for ROM Versions

The ROM-only versions of the MAXQ610 family devices operate in the same manner as their flash counterparts with the following exceptions:

- The ROM loader is not available in the ROM version.
- Loading memory and in-application programming are not supported.
- The debugger is not available in the ROM version.

#### Additional Documentation

Designers must have the following documents to fully use all the features of this device. This data sheet contains pin descriptions, feature overviews, and electrical specifications. Errata sheets contain deviations from published specifications. The user's guides offer detailed information about device features and operation. The following documents can be downloaded from **www.maxim-ic.com/microcontrollers**.

- This MAXQ610 data sheet, which contains electrical/ timing specifications and pin descriptions.
- The MAXQ610 revision-specific errata sheet (www.maxim-ic.com/errata).
- The *MAXQ610 User's Guide*, which contains detailed information on core features and operation, including programming.

#### Development and Technical Support

Maxim and third-party suppliers provide a variety of highly versatile, affordably priced development tools for this microcontroller, including the following:

- Compilers
- In-circuit emulators

- Integrated Development Environments (IDEs)
- JTAG-to-serial converters for programming and debugging

A partial list of development tool vendors can be found at **<u>www.maxim-ic.com/MAXQ\_tools</u>**.

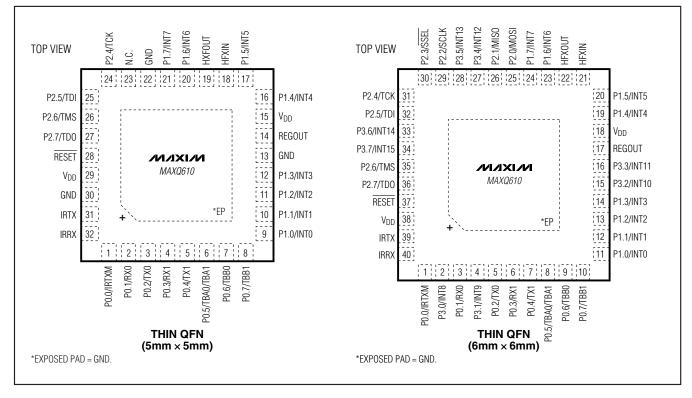
Technical support is available at <u>https://support.maxim-</u> ic.com/micro.

## Selector Guide

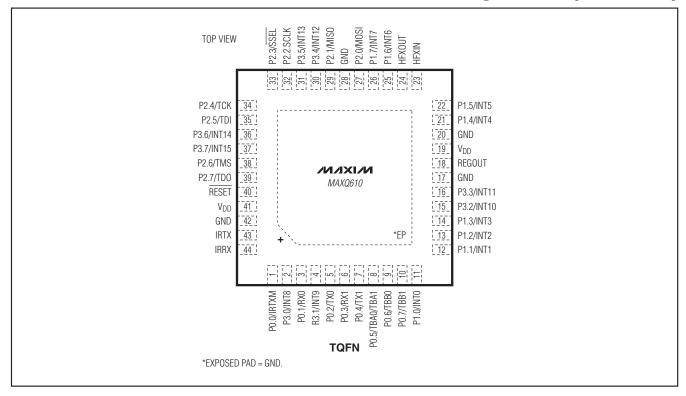
PART	OPERATING VOLTAGE (V)	PROGRAM MEMORY (KB)	DATA MEMORY (KB)	PIN-PACKAGE
MAXQ610A-0000+	1.70 to 3.6	64 Flash	2	32 TQFN-EP
MAXQ610B-0000+	1.70 to 3.6	64 Flash	2	40 TQFN-EP
MAXQ610J-0000+	1.70 to 3.6	64 Flash	2	44 TQFN-EP
MAXQ610X-0000+	1.70 to 3.6	64 Flash	2	Bare die

Note: Contact factory for information about masked ROM devices.

## **Pin Configurations**



#### **Pin Configurations (continued)**



#### Package Information

For the latest package outline information and land patterns (footprints), go to <u>www.maxim-ic.com/packages</u>. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	OUTLINE NO.	LAND PATTERN NO.
32 TQFN-EP	T3255+3	<u>21-0140</u>	<u>90-0001</u>
40 TQFN-EP	T4066+2	<u>21-0141</u>	<u>90-0053</u>
44 TQFN-EP	T4477+2	<u>21-0144</u>	<u>90-0127</u>

MAXQ610

## **Revision History**

REVISION NUMBER	REVISION DATE	DESCRIPTION	
0	10/08	Initial release	—
1	11/08	Removed the SyscIk = 1MHz condition for the Active Current parameter, changed the R <sub>PU</sub> min values from 18k $\Omega$ and 19k $\Omega$ to 16k $\Omega$ and 17k $\Omega$ , and changed the f <sub>NANO</sub> T <sub>A</sub> = +25°C min and max values from 4.2kHz and 14.0kHz to 3.0kHz and 20.0kHz, respectively, in the <i>Recommended DC Operating Conditions</i> table	4, 5
		Added the sentence "Software must configure this pin after release from reset to remove the high-impedance input condition." to the IRRX, P0.x, P1.x, P2.x, and P3.x descriptions in the <i>Pin Description</i> table	8, 9
	1/09	Added future status to the 32 TQFN package in the Ordering Information table	1
2		Changed the REGOUT pin series resistance from $1\Omega$ to $2\Omega$ to $10\Omega$ in the Pin Description table	8
3	7/09	Changed the t <sub>IRRX_A</sub> minimum spec from 200ns to 300ns in the <i>Recommended DC Operating Conditions</i> table	5
		Removed the statement about the use of multilayer boards from the <i>Grounds and Bypassing</i> section	25
4	10/09	Adjusted the minimum resonator frequency from DCMHz to 1MHz and the minimum programming frequency from 5MHz to 6MHz in the <i>Recommended DC Operating Conditions</i> table	5, 6
5	2/10	Added the 44-pin TQFN package	1, 8, 9, 10, 26, 27, 28
6	7/11	Removed future status from the MAXQ610A-0000+ in the Ordering Information table; added the continuous power dissipation, lead temperature, and soldering temperature information to the Absolute Maximum Ratings section	1, 4

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.